Artur Tuktamyshev

List of Publications by Year
in descending order

22	147	1307366 7	1199470 12
papers	citations	h-index	g-index

22	22	22	142
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Optically controlled dual-band quantum dot infrared photodetector. Nanomaterials and Nanotechnology, 2022, 12, 184798042210857.	1.2	2
2	Controlling the threshold voltage of a semiconductor field-effect transistor by gating its graphene gate. Npj 2D Materials and Applications, 2022, 6, .	3.9	6
3	Nucleation of Ga droplets self-assembly on GaAs(111)A substrates. Scientific Reports, 2021, 11, 6833.	1.6	6
4	Telecom-wavelength InAs QDs with low fine structure splitting grown by droplet epitaxy on GaAs(111)A vicinal substrates. Applied Physics Letters, 2021, 118, .	1.5	12
5	Reentrant Behavior of the Density vs. Temperature of Indium Islands on GaAs(111)A. Nanomaterials, 2020, 10, 1512.	1.9	2
6	Highâ€“temperature droplet epitaxy of symmetric GaAs/AlGaAs quantum dots. Scientific Reports, 2020, 10, 6532.	1.6	22
7	Spectral broadening in self-assembled GaAs quantum dots with narrow size distribution. Journal of Applied Physics, 2019, 126, .	1.1	13
8	Temperature Activated Dimensionality Crossover in the Nucleation of Quantum Dots by Droplet Epitaxy on GaAs(111)A Vicinal Substrates. Scientific Reports, 2019, 9, 14520.	1.6	11
9	Pseudomorphic GeSiSn, SiSn and Ge layers in strained heterostructures. Nanotechnology, 2018, 29, 154002.	1.3	19
10	Effect of a Stepped Si(100) Surface on the Nucleation Process of Ge Islands. Russian Physics Journal, 2018, 60, 1864-1870.	0.2	1
11	Formation of a Stepped Si(100) Surface and Its Effect on the Growth of Ge Islands. Semiconductors, 2018, 52, 390-393.	0.2	0
12	Morphology, Structure, and Optical Properties of Semiconductor Films with GeSiSn Nanoislands and Strained Layers. Nanoscale Research Letters, 2018, 13, 29.	3.1	15
13	Self-assembled strained GeSiSn nanoscale structures grown by MBE on Si(100). Journal of Crystal Growth, 2017, 457, 215-219.	0.7	5
14	Valence-band offsets in strained SiGeSn/Si layers with different tin contents. Semiconductors, 2017, 51, 329-334.	0.2	2
15	Splitting of frequencies of optical phonons in tensile-strained germanium layers. JETP Letters, 2017, 105, 327-331.	0.4	15
16	The ordering of Ge islands on a stepped Si(100) surface. Journal of Physics: Conference Series, 2017, 816, 012015.	0.3	0
17	Elastically strained GeSiSn layers and GeSiSn islands in multilayered periodical structures. Modern Electronic Materials, 2017, 3, 86-90.	0.2	0
18	Sn influence on MBE growth of GeSiSn/Si MQW. Journal of Physics: Conference Series, 2017, 816, 012020.	0.3	3

#	Article	IF	Citations
19	Growth of Epitaxial SiSn Films with High Sn Content for IR Converters. Russian Physics Journal, 2017, 60, 354-359.	0.2	5
20	Strained multilayer structures with pseudomorphic GeSiSn layers. Semiconductors, 2016, 50, 1584-1588.	0.2	5
21	Initial growth stages of Siâ€“Geâ€“Sn ternary alloys grown on Si (100) by low-temperature molecular-beam epitaxy. Semiconductors, 2015, 49, 1582-1586.	0.2	3
22	Synthesis of Epitaxial Films Based on Geâ€“Siâ€“Sn Materials with Ge/GeSn, Ge/GeSiSn, and GeSn/GeSiSn Heterojunctions. Russian Physics Journal, 2015, 58, 965-969.	0.2	0